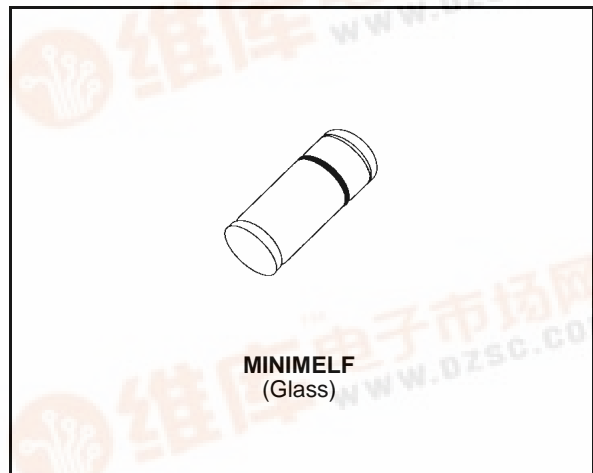




# TMMBAT 42 TMMBAT 43

## SMALL SIGNAL SCHOTTKY DIODES



### DESCRIPTION

General purpose, metal to silicon diodes featuring very low turn-on voltage fast switching.

These devices have integrated protection against excessive voltage such as electrostatic discharges.

### ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive Peak Reverse Voltage		30	V
$I_F$	Forward Continuous Current	$T_I = 25\text{ }^\circ\text{C}$	200	mA
$I_{FRM}$	Repetitive Peak Forward Current	$t_p \leq 1\text{ s}$ $\delta \leq 0.5$	500	mA
$I_{FSM}$	Surge non Repetitive Forward Current	$t_p = 10\text{ ms}$	4	A
$P_{tot}$	Power Dissipation	$T_I = 65\text{ }^\circ\text{C}$	200	mW
$T_{stg}$ $T_j$	Storage and Junction Temperature Range		- 65 to 150 - 65 to 125	$^\circ\text{C}$ $^\circ\text{C}$
$T_L$	Maximum Temperature for Soldering during 15s		260	$^\circ\text{C}$

### THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-l)}$	Junction-leads	300	$^\circ\text{C/W}$



# TMMBAT 42/TMMBAT 43

## ELECTRICAL CHARACTERISTICS

### STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
$V_{BR}$	$T_j = 25^\circ\text{C}$	$I_R = 100\mu\text{A}$	30			V
$V_F^*$	$T_j = 25^\circ\text{C}$	$I_F = 200\text{mA}$	All Types		1	V
	$T_j = 25^\circ\text{C}$	$I_F = 10\text{mA}$	BAT 42		0.4	
	$T_j = 25^\circ\text{C}$	$I_F = 50\text{mA}$			0.65	
	$T_j = 25^\circ\text{C}$	$I_F = 2\text{mA}$	BAT 43		0.26	
	$T_j = 25^\circ\text{C}$	$I_F = 15\text{mA}$			0.45	
$I_R^*$	$T_j = 25^\circ\text{C}$	$V_R = 25\text{V}$			0.5	$\mu\text{A}$
	$T_j = 100^\circ\text{C}$				100	

### DYNAMIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
C	$T_j = 25^\circ\text{C}$	$V_R = 1\text{V}$ $f = 1\text{MHz}$		7		pF
$t_{rr}$	$T_j = 25^\circ\text{C}$	$I_F = 10\text{mA}$ $I_R = 10\text{mA}$ $i_{rr} = 1\text{mA}$ $R_L = 100\Omega$			5	ns
$\eta$	$T_j = 25^\circ\text{C}$	$R_L = 15\text{K}\Omega$ $C_L = 300\text{pF}$ $f = 45\text{MHz}$ $V_i = 2\text{V}$	80			%

\* Pulse test:  $t_p \leq 300\mu\text{s}$   $\delta < 2\%$ .

Figure 1. Forward current versus forward voltage at different temperatures (typical values).

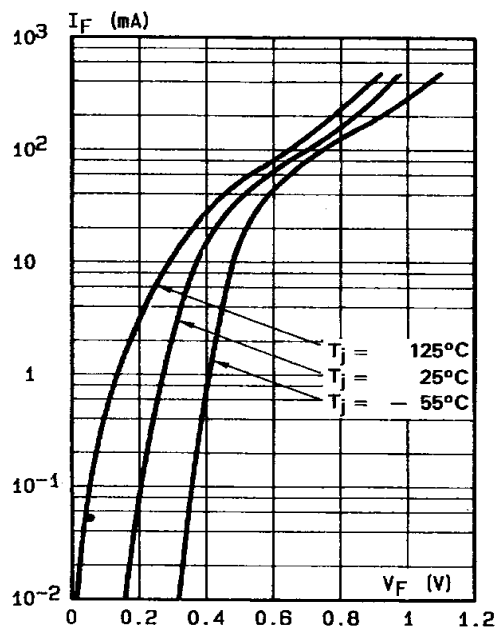


Figure 2. Forward current versus forward voltage (typical values).

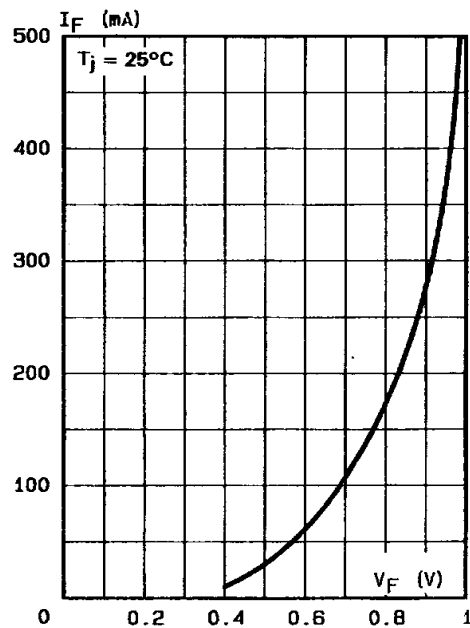


Figure 3. Reverse current versus junction temperature.

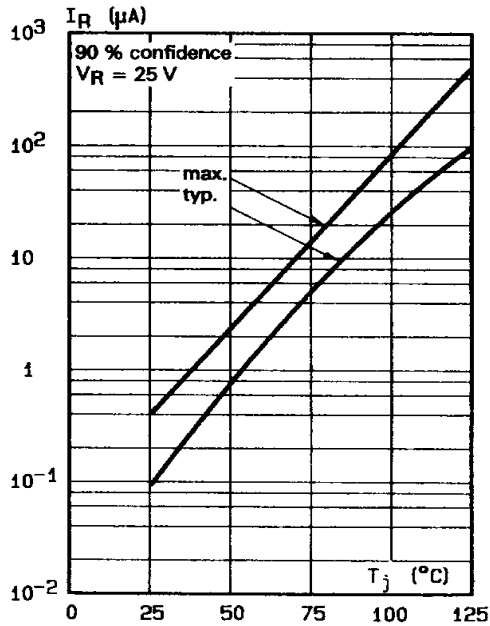


Figure 4. Reverse current versus continuous reverse voltage (typical values).

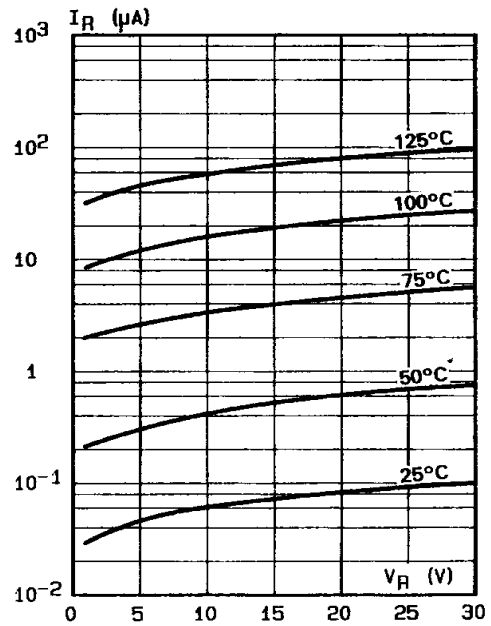
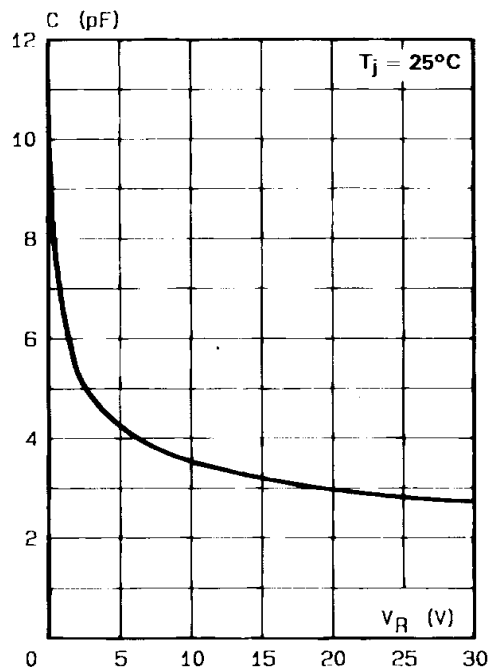


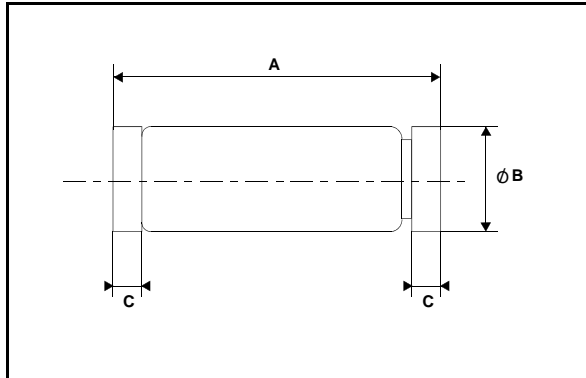
Figure 5. Forward current versus forward voltage (typical values).



## TMMBAT 42/TMMBAT 43

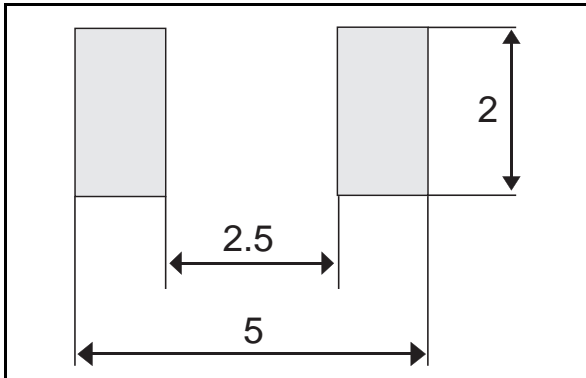
### PACKAGE MECHANICAL DATA

#### MINIMELF Glass



REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	3.30	3.40	3.6	0.130	0.134	0.142
B	1.59	1.60	1.62	0.063	0.063	0.064
C	0.40	0.45	0.50	0.016	0.018	0.020
D		1.50			0.059	

#### FOOT PRINT DIMENSIONS (Millimeter)



Marking: ring at cathode end.  
Weight: 0.05g

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